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1	BRS	L6	137	(empirical data) same wafer same simulation same semiconductor	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	2007/01/19 12:03
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4	BRS	L9	4	(empirical adj data) same wafer same simulation	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	2007/01/19 12:06
5	BRS	L10	10	(empirical adj data) same semiconductor same simulation	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	2007/01/19 12:06



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[\*\*A GENERIC SYSTEM SIMULATOR WITH NOVEL ON-CHIP CACHE AND THROUGHPUT MODELS FOR GIGASCALE INTEGRATION\*\* - group of 5 »](#)

JC Eble III - 1998 - gigascale.org

... like to acknowledge the **Semiconductor Research Corporation** ... University System Performance

**Simulator (SUSPENS)....13 ... TIER CONSISTS OF ONE PHYSICAL LEVEL ...**

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[\*\*Worst case design parameter extraction for logic technologies\*\* - group of 3 »](#)

Z Krivokapic, WD Heavlin - US Patent 6,304,836, 2001 - Google Patents

... For example, the **semiconductor device simulator** may require ... Some of these parameters

may correspond to **physical** measurements of the device 200, such as ...

Cited by 5 - Related Articles - Web Search

[\*\*Analysis of mixed-signal manufacturability with statisticaltechnology CAD \(TCAD\)\*\* - group of 3 »](#)

DA Hanson, RJJ Goossens, M Redford, J McGinty, JK ... - **Semiconductor Manufacturing**, IEEE Transactions on, 1996 - ieeexplore.ieee.org

... normally determined from destructive **physical** measurements or ... by 1M0B33, a National

**Semiconductor** proprietary model ... the process and device **simulation**) takes 15 ...

Cited by 11 - Related Articles - Web Search - BL Direct

[\*\*Atomistic simulation of ion implantation and its application in Si technology\*\* - group of 3 »](#)

M Posselt, B Schmidt, T Feudel, N Strecker - Materials Science and Engineering B, 2000 - elsevier.com

... the collection of a huge amount of **empirical data** on the ... The **physical** reason for the success of this model ... In the computer **simulation** of ion implantation into ...

Cited by 17 - Related Articles - View as HTML - Web Search

[\*\*Materials theory based modeling of wide band gap semiconductors: from basic properties to devices\*\* - group of 2 »](#)

KF Brennan, E Bellotti, M Farahmand, J Haralson, ... - Solid State Electronics, 2000 - Elsevier

... approximate since it neglects many important **physical** effects such as ... illustrated its application in the **simulation** of various **semiconductor** devices through ...

Cited by 15 - Related Articles - Web Search - BL Direct

[\*\*Manufacturability Metrics and RET Tradeoffs For Physical Design and Layout\*\*](#)

L Capodieci - Electronic Design Processes, 2003 - eda.org

... **semiconductor** manufacturing costs for traditionally designed systems ... s set is released and **physical** designs are ... DR k a. Perform process **simulation** b. Extract ...

Cited by 2 - Related Articles - View as HTML - Web Search

TEM 2 P 2 EST: A Thermal Enabled Multi-Model Power/Performance ESTimator - group of 4 »

A Dhodapkar, CH Lim, G Cai, WR Daasch - Proc. PACS, 2000 - Springer

... the configuration file contains **physical** structure data ... These two **simulation** modes can be used ... domain data from TSMC (Taiwan **Semiconductor** Manufacturing Company ...

Cited by 57 - Related Articles - Web Search - BL Direct

Lump Partitioning of IC Bipolar Transistor Models for High-Frequency Applications - group of 4 »

NN Chan, RW Dutton - ieeexplore.ieee.org

... parameter data taken from devices is compared to that generated from a two-lump model predicted by **physical** theory using 2-D finite element device **simulation** ...

Cited by 1 - Related Articles - Web Search

Forecasting method for HEMT MMIC large-signal RF yield

R Tsai, YC Chen, M Nishimoto, LW Yang, W Okamura, ... - ieeexplore.ieee.org

... We have found that Semi-**Physical** device modeling ... T. Ytterdal, and K. Lee, **Semiconductor**

Device Modeling for ... [4] H. R. Yeager, "Circuit **simulation** models for ...

Cited by 1 - Related Articles - Web Search

Intrafield Effects on Device and Circuit Manufacturability: A Statistical Simulation Approach - group of 4 »

Z Krivokapic, WD Heavlin - IEEE TRANSACTIONS ON SEMICONDUCTOR MANUFACTURING, 1999 - ieeexplore.ieee.org

... the configuration of runs from the **physical** simulators ... with the least number of reactor **simulation** runs ... 444 IEEE TRANSACTIONS ON SEMICONDUCTOR MANUFACTURING, VOL ...

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